TH 2302

MICROWAVE NPN POWER TRANSISTOR FOR CLASS C OPERATION

TRANSISTOR NPN HYPERFREQUENCE DE PUISSANCE, CLASSE C

FEATURES

- Gold metallizations
- Glass passivated structure
- Hermetical ceramic package

→ high reliability

- Emitter ballast resistors → severe impedance mismatch
- Auto-aligned structure → high characteristics reproductibility

APPLICATIONS

Telecommunications up to 2,3 GHz frequency band.

PARTICULARITES

- *Métallisations "Or"*
- *Structure passivée*
- *Boîtier céramique hermétique*

→ *haute fiabilité*

- *Résistances ballast d'émetteur* → *bonne tenue au ROS*
- *Structure auto-alignée* → *bonne reproductibilité des caractéristiques*

APPLICATIONS

Télécommunications dans la bande de fréquences jusqu'à 2,3 GHz

f	=	2,3 GHz
P_{OUT}	=	1,75 W
G_P	=	9,5 dB
η_c	=	40 %
V_{CC}	=	24 V

Case / *Boîtier* : CB-294 (.2502LFL/FLM)
CB-311 (.2502L/2LM)

ABSOLUTE RATINGS (LIMITING VALUES) / ***VALEURS LIMITES ABSOLUES D'UTILISATION***	Symbols	Values	Units
Emitter-base (d.c.) voltage / *Tension continue émetteur-base*	V_{EBO}	3	V
Collector-base (d.c.) voltage / *Tension continue collecteur-base*	V_{CBO}	45	V
Collector-emitter (d.c.) voltage / *Tension continue collecteur-émetteur*	V_{CES}	45	V
Collector (d.c.) current / *Courant continu de collecteur*	I_C	0,4	A
Storage and junction temperature range / *Températures extrêmes de stockage et de jonction*	T_{stg} T_j	— 65 → + 200 — 55 → + 200	°C °C

Thermal resistance (junction-case) / *Résistance thermique (jonction-boîtier)*	$R_{th(j-c)}$	30	°C/W

January 1981 - 1/4

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STATIC CHARACTERISTICS at t_{amb} = 25°C
CARACTERISTIQUES STATIQUES à t_{amb} = 25°C

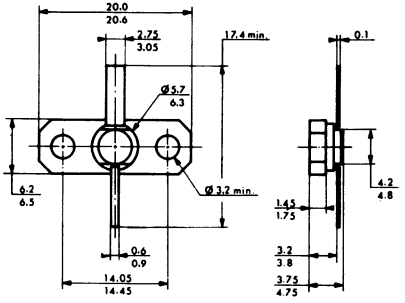
Symbols	Values			Units	Test conditions
	min.	typ.	max.		
$V_{(BR)EBO}$	3			V	I_E = 1 mA
$V_{(BR)CBO}$				V	I_C = mA
$V_{(BR)CES}$	45			V	I_C = 5 mA
I_{CBO}			1	mA	V_{CB} = 24 V
H_{FE}	15		120		I_C = 100 mA V_{CE} = 5 V
C_{22b}			3,5	pF	V_{CB} = 24 V f = 1 MHz

DYNAMIC CHARACTERISTICS at t_{amb} = 25°C
CARACTERISTIQUES DYNAMIQUES à t_{amb} = 25°C

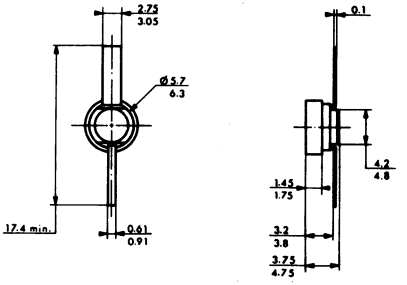
Symbols	Values			Units	Test conditions
	min.	typ.	max.		
P_{OUT}	1,6	1,75		W	f = 2,3 GHz V_{CC} = 24 V P_{IN} = 0,2 W
G_P	9	9,5		dB	f = 2,3 GHz V_{CC} = 24 V P_{IN} = 0,2 W
η_c	36	40		%	f = 2,3 GHz V_{CC} = 24 V P_{IN} = 0,2 W

CASE DESCRIPTION
DESCRIPTION DU BOITIER

CB-294 (.2502LFL/FLM, BMH 75 a)



CB-311 (.2502L/2LM, BMH 75 b)



Dimensions in millimeters

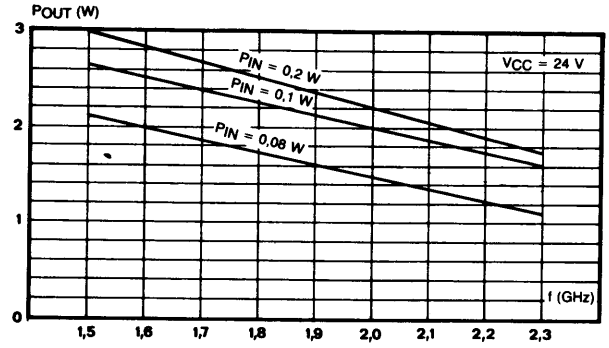


Fig. 1 - Output power versus frequency (typical values).

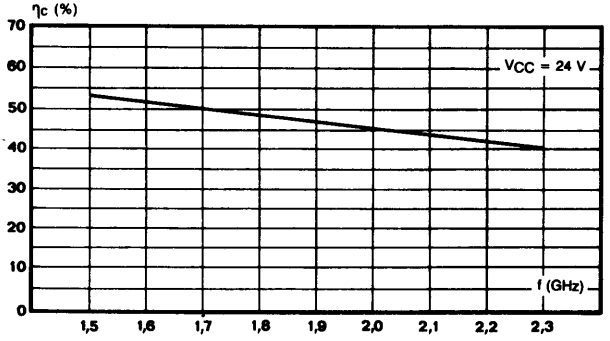


Fig. 2 - Collector efficiency versus frequency (typical values).

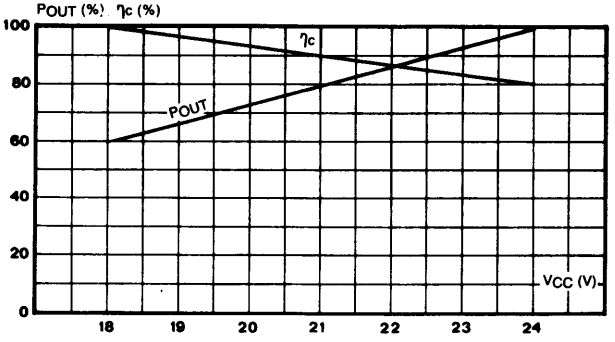


Fig. 3 - Relative output power and relative collector efficiency versus collector voltage.

Z_{IN} : Input impedance
Z_{CL} : Collector load impedance

V_{CC} = 24 V
P_{IN} = 0,2 W
Z_O = 50Ω

Fig. 4 - Smith chart

THOMSON-CSF

DIVISION SEMICONDUCTEURS DISCRETS

TH 2304

MICROWAVE NPN POWER TRANSISTOR FOR CLASS C OPERATION

TRANSISTOR NPN HYPERFREQUENCE DE PUISSANCE, CLASSE C

FEATURES

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- Emitter ballast resistors → severe impedance mismatch
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APPLICATIONS

Telecommunications up to 2,3 GHz frequency band.

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APPLICATIONS

Télécommunications dans la bande de fréquences jusqu'à 2,3 GHz

f	=	2,3 GHz
POUT	=	3,5 W
GP	=	8,5 dB
η_c	=	40 %
VCC	=	24 V

Case / *Boîtier* : CB-294 (.2502LFL/FLM)
CB-311 (.2502L/2LM)

ABSOLUTE RATINGS (LIMITING VALUES) / ***VALEURS LIMITES ABSOLUES D'UTILISATION***	Symbols	Values	Units
Emitter-base (d.c.) voltage *Tension continue émetteur-base*	V_{EBO}	3	V
Collector-base (d.c.) voltage *Tension continue collecteur-base*	V_{CBO}	45	V
Collector-emitter (d.c.) voltage *Tension continue collecteur-émetteur*	V_{CES}	45	V
Collector (d.c.) current *Courant continu de collecteur*	I_C	0,8	A
Storage and junction temperature range *Températures extrêmes de stockage et de jonction*	T_{stg} T_j	— 65 → + 200 — 55 → + 200	°C °C

Thermal resistance (junction-case) *Résistance thermique (jonction-boîtier)*	$R_{th(j-c)}$	17	°C/W

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THOMSON-CSF
COMPOSANTS

STATIC CHARACTERISTICS at t_{amb} = 25°C
CARACTERISTIQUES STATIQUES à t_{amb} = 25°C

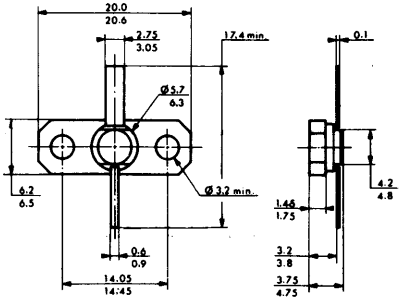
Symbols	Values			Units	Test conditions		
	min.	typ.	max.				
$V_{(BR)EBO}$	3			V	I_E = 2,5 mA		
$V_{(BR)CBO}$				V	I_C = mA		
$V_{(BR)CES}$	45			V	I_C = 10 mA		
I_{CBO}			2,5	mA	V_{CB} = 24 V		
H_{FE}	15		120		I_C = 250 mA	V_{CE} = 5 V	
C_{22b}			5,5	pF	V_{CB} = 24 V	f = 1 MHz	

DYNAMIC CHARACTERISTICS at t_{amb} = 25°C
CARACTERISTIQUES DYNAMIQUES à t_{amb} = 25°C

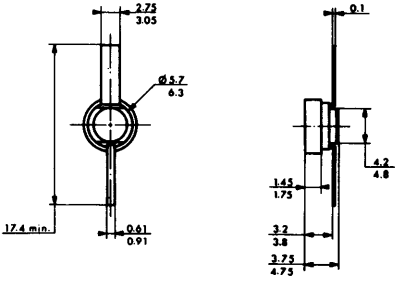
Symbols	Values			Units	Test conditions		
	min.	typ.	max.				
P_{OUT}	3,2	3,5		W	f = 2,3 GHz	V_{CC} = 24 V	P_{IN} = 0,5 W
G_P	8	8,5		dB	f = 2,3 GHz	V_{CC} = 24 V	P_{IN} = 0,5 W
η_c	36	40		%	f = 2,3 GHz	V_{CC} = 24 V	P_{IN} = 0,5 W

CASE DESCRIPTION
DESCRIPTION DU BOITIER

CB-294 (.2502LFL/FLM, BMH 75 a)



CB-311 (.2502L/2LM, BMH 75 b)



Dimensions in millimeters

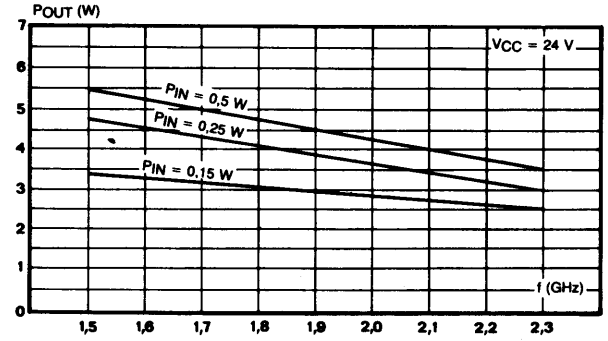


Fig. 1 - Output power versus frequency (typical values).

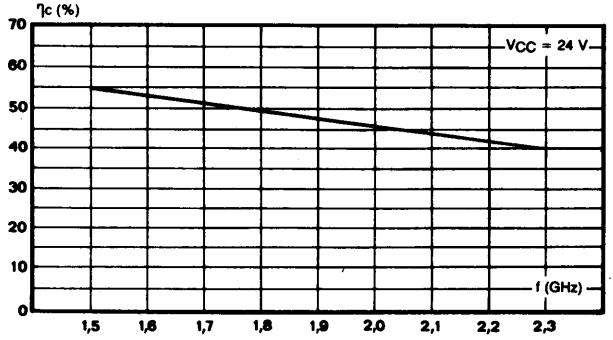


Fig. 2 - Collector efficiency versus frequency (typical values).

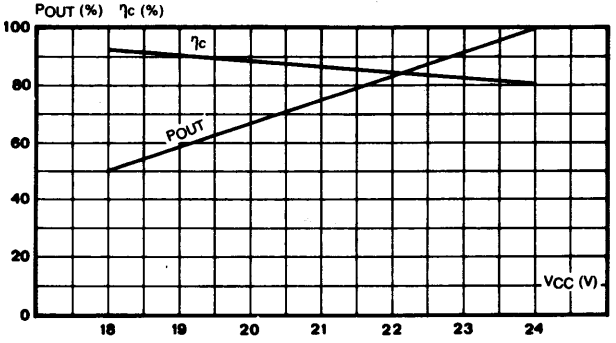


Fig. 3 - Relative output power and relative collector efficiency versus collector voltage.

Z_{IN} : Input impedance
Z_{CL} : Collector load impedance

V_{CC} = 24 V
P_{IN} = 0,5 W
Z_O = 50Ω

Fig. 4 - Smith chart

THOMSON-CSF
DIVISION SEMICONDUCTEURS DISCRETS

TH 2307

MICROWAVE NPN POWER TRANSISTOR FOR CLASS C OPERATION
TRANSISTOR NPN HYPERFREQUENCE DE PUISSANCE, CLASSE C

FEATURES

- Gold metallizations
- Glass passivated structure
- Hermetical ceramic package

→ high reliability

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APPLICATIONS

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- *Résistances ballast d'émetteur* → *bonne tenue au ROS*
- *Structure auto-alignée* → *bonne reproductibilité des caractéristiques*

APPLICATIONS

Télécommunications dans la bande de fréquences jusqu'à 2,3 GHz

f	=	2,3 GHz
P_{OUT}	=	7 W
G_P	=	8,5 dB
η_c	=	40 %
V_{CC}	=	24 V

Case / *Boîtier* : CB-294 (.2502LFL/FLM)
CB-311 (.2502L/2LM)

ABSOLUTE RATINGS (LIMITING VALUES) / ***VALEURS LIMITES ABSOLUES D'UTILISATION***	Symbols	Values	Units
Emitter-base (d.c.) voltage / *Tension continue émetteur-base*	V_{EBO}	3	V
Collector-base (d.c.) voltage / *Tension continue collecteur-base*	V_{CBO}	45	V
Collector-emitter (d.c.) voltage / *Tension continue collecteur-émetteur*	V_{CES}	45	V
Collector (d.c.) current / *Courant continu de collecteur*	I_C	1,5	A
Storage and junction temperature range / *Températures extrêmes de stockage et de jonction*	T_{stg} T_j	— 65 → + 200 — 55 → + 200	°C °C

Thermal resistance (junction-case) / *Résistance thermique (jonction-boîtier)*	$R_{th(j-c)}$	8,5	°C/W

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THOMSON-CSF COMPOSANTS

STATIC CHARACTERISTICS at t_{amb} = 25°C
CARACTERISTIQUES STATIQUES à t_{amb} = 25°C

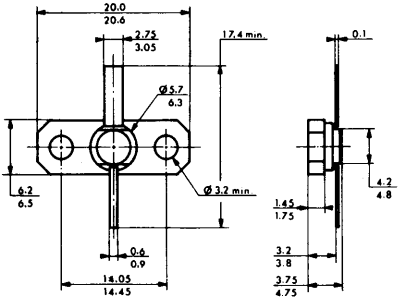
Symbols	Values			Units	Test conditions	
	min.	typ.	max.			
$V_{(BR)EBO}$	3			V	I_E = 5 mA	
$V_{(BR)CBO}$				V	I_C = mA	
$V_{(BR)CES}$	45			V	I_C = 25 mA	
I_{CBO}			5	mA	V_{CB} = 24 V	
H_{FE}	15		120		I_C = 500 mA	V_{CE} = 5 V
C_{22b}			8	pF	V_{CB} = 24 V	f = 1 MHz

DYNAMIC CHARACTERISTICS at t_{amb} = 25°C
CARACTERISTIQUES DYNAMIQUES à t_{amb} = 25°C

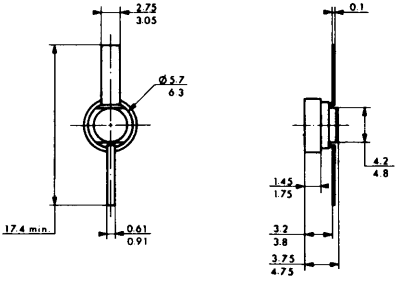
Symbols	Values			Units	Test conditions		
	min.	typ.	max.				
P_{OUT}	6,3	7		W	f = 2,3 GHz	V_{CC} = 24 V	P_{IN} = 1 W
G_P	8	8,5		dB	f = 2,3 GHz	V_{CC} = 24 V	P_{IN} = 1 W
η_c	36	40		%	f = 2,3 GHz	V_{CC} = 24 V	P_{IN} = 1 W

CASE DESCRIPTION
DESCRIPTION DU BOITIER

CB-294 (.2502LFL/FLM, BMH 75 a)



CB-311 (.2502L/2LM, BMH 75 b)



Dimensions in millimeters

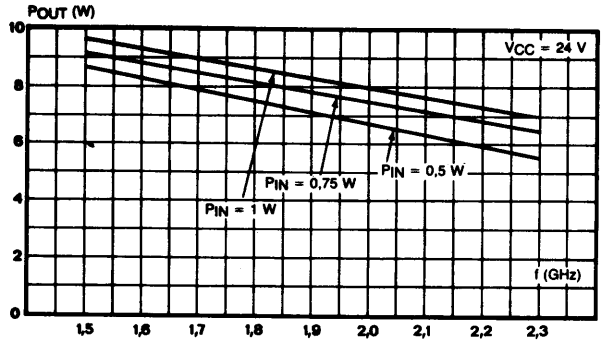


Fig. 1 - Output power versus frequency (typical values).

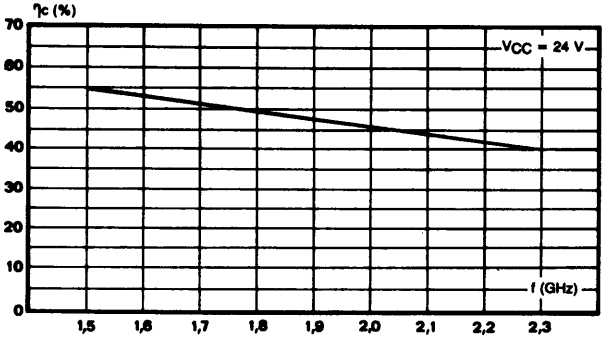


Fig. 2 - Collector efficiency versus frequency (typical values).

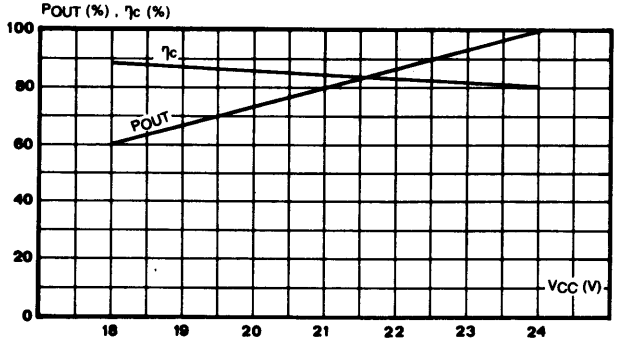


Fig. 3 - Relative output power and relative collector efficiency versus collector voltage.

Z_{IN} : Input impedance
Z_{CL} : Collector load impedance

Fig. 4 - Smith chart

THOMSON-CSF
DIVISION SEMICONDUCTEURS DISCRETS

TH 3000

MICROWAVE NPN POWER TRANSISTOR FOR CLASS C OPERATION
TRANSISTOR NPN HYPERFREQUENCE DE PUISSANCE, CLASSE C

FEATURES

- Gold metallizations
- Glass passivated structure
- Hermetical ceramic package

→ high reliability

- Emitter ballast resistors → severe impedance mismatch
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APPLICATIONS

Telecommunications up to 3 GHz frequency band.

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- *Structure auto-alignée* → *bonne reproductibilité des caractéristiques*

APPLICATIONS

Télécommunications dans la bande de fréquences jusqu'à 3 GHz

f	=	3 GHz
P_{OUT}	=	0,55 W
G_P	=	7,4 db
η_c	=	25 %
V_{CC}	=	28 V

Case / *Boîtier* : CB-294 (.2502LFL/FLM)
CB-311 (.2502L/2LM)

ABSOLUTE RATINGS (LIMITING VALUES) ***VALEURS LIMITES ABSOLUES D'UTILISATION***	Symbols	Values	Units
Emitter-base (d.c.) voltage *Tension continue émetteur-base*	V_{EBO}	3	V
Collector-base (d.c.) voltage *Tension continue collecteur-base*	V_{CBO}	50	V
Collector-emitter (d.c.) voltage *Tension continue collecteur-émetteur*	V_{CES}	50	V
Collector (d.c.) current *Courant continu de collecteur*	I_C	0,15	A
Storage and junction temperature range *Températures extrêmes de stockage et de jonction*	T_{stg} T_j	— 65 → + 200 — 55 → + 200	°C °C

Thermal resistance (junction-case) *Résistance thermique (jonction-boîtier)*	$R_{th(j-c)}$	45	°C/W

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THOMSON-CSF COMPOSANTS

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CARACTERISTIQUES STATIQUES à t_{amb} = 25°C

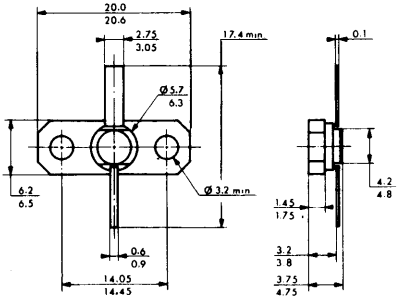
Symbols	Values			Units	Test conditions
	min.	typ.	max.		
$V_{(BR)EBO}$	3			V	I_E = 0,5 mA
$V_{(BR)CBO}$				V	I_C = mA
$V_{(BR)CES}$	50			V	I_C = 5 mA
I_{CBO}			0,5	mA	V_{CB} = 28 V
H_{FE}	15		120		I_C = 50 mA V_{CE} = 5 V
C_{22b}			2,5	pF	V_{CB} = 28 V f = 1 MHz

DYNAMIC CHARACTERISTICS at t_{amb} = 25°C
CARACTERISTIQUES DYNAMIQUES à t_{amb} = 25°C

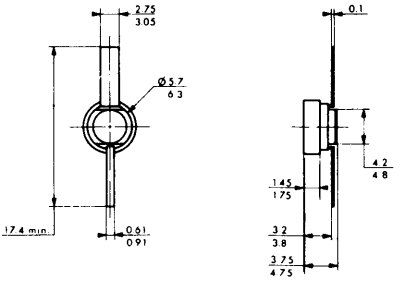
Symbols	Values			Units	Test conditions
	min.	typ.	max.		
P_{OUT}	0,5	0,55		W	f = 3 GHz V_{CC} = 28 V P_{IN} = 0,1 W
G_P	7	7,4		dB	f = 3 GHz V_{CC} = 28 V P_{IN} = 0,1 W
η_c	22,5	25		%	f = 3 GHz V_{CC} = 28 V P_{IN} = 0,1 W

CASE DESCRIPTION
DESCRIPTION DU BOITIER

CB-294 (.2502LFL/FLM, BMH 75 a)



CB-311 (.2502L/2LM, BMH 75 b)



Dimensions in millimeters

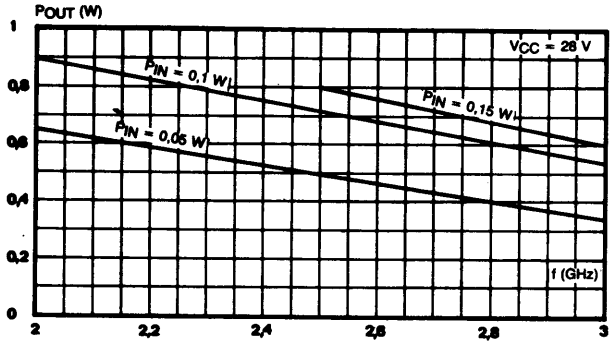


Fig. 1 - Output power versus frequency (typical values).

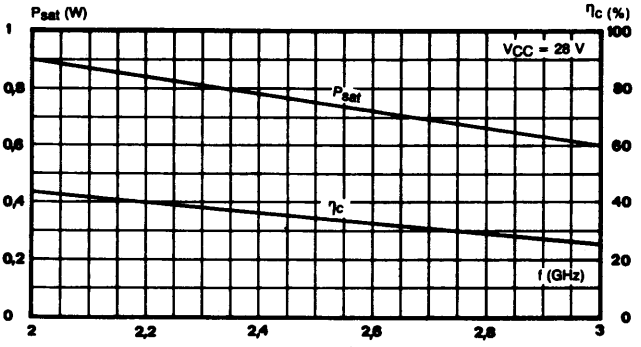


Fig. 2 - Collector efficiency and saturation power versus frequency (typical values).

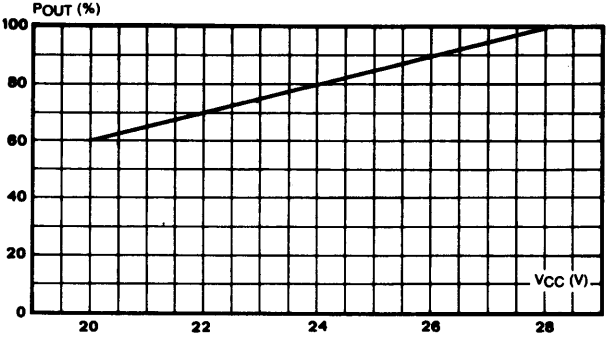


Fig. 3 - Relative output power versus collector voltage.

Z_{IN} : Input impedance
Z_{CL} : Collector load impedance

V_{CC} = 28 V
P_{IN} = 0,1 W
Z_O = 50Ω

Fig. 4 - Smith chart

THOMSON-CSF

DIVISION SEMICONDUCTEURS DISCRETS

TH 3001

MICROWAVE NPN POWER TRANSISTOR FOR CLASS C OPERATION

TRANSISTOR NPN HYPERFREQUENCE DE PUISSANCE, CLASSE C

FEATURES

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- *Structure auto-alignée* → *bonne reproductibilité des caractéristiques*

APPLICATIONS

Télécommunications dans la bande de fréquences jusqu'à 3 GHz

f	=	3	GHz
P_{OUT}	=	1	W
G_P	=	7	dB
η_c	=	30	%
V_{CC}	=	28	V

Case / *Boîtier* : CB-294 (.2502LFL/FLM)
CB-311 (.2502L/2LM)

ABSOLUTE RATINGS (LIMITING VALUES) ***VALEURS LIMITES ABSOLUES D'UTILISATION***	Symbols	Values	Units
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Collector-base (d.c.) voltage *Tension continue collecteur-base*	V_{CBO}	50	V
Collector-emitter (d.c.) voltage *Tension continue collecteur-émetteur*	V_{CES}	50	V
Collector (d.c.) current *Courant continu de collecteur*	I_C	0,4	A
Storage and junction temperature range *Températures extrêmes de stockage et de jonction*	T_{stg} T_j	— 65 → + 200 — 55 → + 200	°C °C

Thermal resistance (junction-case) *Résistance thermique (jonction-boîtier)*	$R_{th(j-c)}$	30	°C/W

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THOMSON-CSF COMPOSANTS

STATIC CHARACTERISTICS at t_{amb} = 25°C
CARACTERISTIQUES STATIQUES à t_{amb} = 25°C

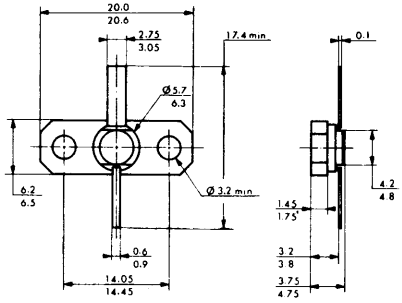
Symbols	Values			Units	Test conditions	
	min.	typ.	max.			
$V_{(BR)EBO}$	3			V	I_E = 1 mA	
$V_{(BR)CBO}$				V	I_C = mA	
$V_{(BR)CES}$	50			V	I_C = 10 mA	
I_{CBO}			1	mA	V_{CB} = 28 V	
H_{FE}	15		120		I_C = 100 mA	V_{CE} = 5 V
C_{22b}			3	pF	V_{CB} = 28 V	f = 1 MHz

DYNAMIC CHARACTERISTICS at t_{amb} = 25°C
CARACTERISTIQUES DYNAMIQUES à t_{amb} = 25°C

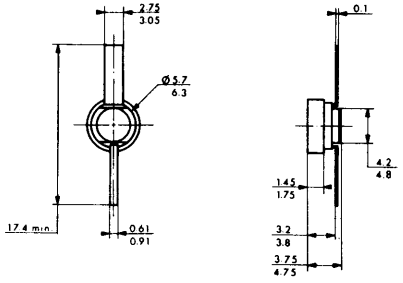
Symbols	Values			Units	Test conditions		
	min.	typ.	max.				
P_{OUT}	0,9	1		W	f = 3 GHz	V_{CC} = 28 V	P_{IN} = 0,2 W
G_P	6,5	7		dB	f = 3 GHz	V_{CC} = 28 V	P_{IN} = 0,2 W
η_c	27	30		%	f = 3 GHz	V_{CC} = 28 V	P_{IN} = 0,2 W

CASE DESCRIPTION
DESCRIPTION DU BOITIER

CB-294 (.2502LFL/FLM, BMH 75 a)



CB-311 (.2502L/2LM, BMH 75 b)



Dimensions in millimeters

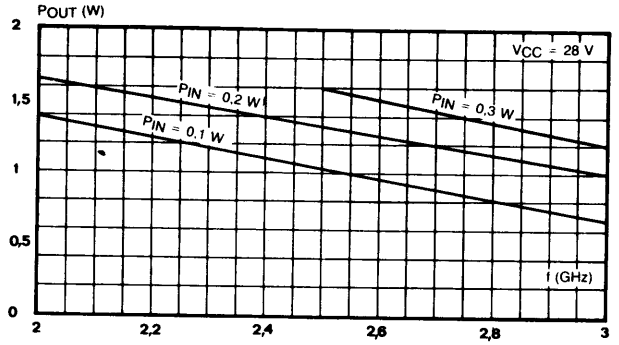


Fig. 1 - Output power versus frequency (typical values).

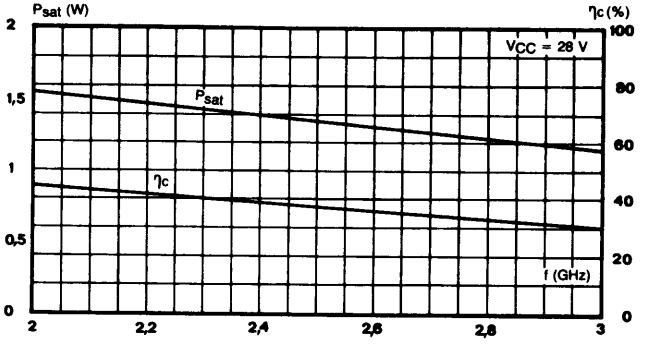


Fig. 2 - Collector efficiency and saturation power versus frequency (typical values).

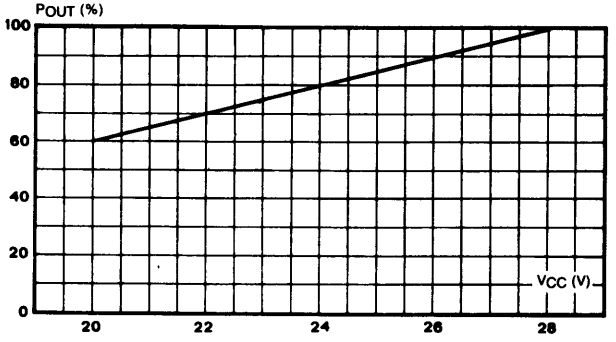


Fig. 3 - Relative output power versus collector voltage.

Fig. 4 - Smith chart

THOMSON-CSF

DIVISION SEMICONDUCTEURS DISCRETS

TH 3003

MICROWAVE NPN POWER TRANSISTOR FOR CLASS C OPERATION

TRANSISTOR NPN HYPERFREQUENCE DE PUISSANCE, CLASSE C

FEATURES

- Gold metallizations
- Glass passivated structure
- Hermetical ceramic package

→ high reliability

- Emitter ballast resistors → severe impedance mismatch
- Auto-aligned structure → high characteristics reproductibility

APPLICATIONS

Telecommunications up to 3 GHz frequency band.

PARTICULARITES

- *Métallisations "Or"*
- *Structure passivée*
- *Boîtier céramique hermétique*

→ *haute fiabilité*

- *Résistances ballast d'émetteur* → *bonne tenue au ROS*
- *Structure auto-alignée* → *bonne reproductibilité des caractéristiques*

APPLICATIONS

Télécommunications dans la bande de fréquences jusqu'à 3 GHz

f	=	3 GHz
P_{OUT}	=	3 W
G_P	=	6 dB
η_c	=	30 %
V_{CC}	=	28 V

Case / ***Boîtier*** : CB-294 (.2502LFL/FLM)
CB-311 (.2502L/2LM)

ABSOLUTE RATINGS (LIMITING VALUES) / ***VALEURS LIMITES ABSOLUES D'UTILISATION***	Symbols	Values	Units
Emitter-base (d.c.) voltage / *Tension continue émetteur-base*	V_{EBO}	3	V
Collector-base (d.c.) voltage / *Tension continue collecteur-base*	V_{CBO}	50	V
Collector-emitter (d.c.) voltage / *Tension continue collecteur-émetteur*	V_{CES}	50	V
Collector (d.c.) current / *Courant continu de collecteur*	$I_{C\,O}$	0,8	A
Storage and junction temperature range / *Températures extrêmes de stockage et de jonction*	T_{stg} T_j	— 65 → + 200 — 55 → + 200	°C °C

Thermal resistance (junction-case) / *Résistance thermique (jonction-boîtier)*	$R_{th(j-c)}$	17	°C/W

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THOMSON-CSF
COMPOSANTS

STATIC CHARACTERISTICS at t_{amb} = 25°C
CARACTERISTIQUES STATIQUES à t_{amb} = 25°C

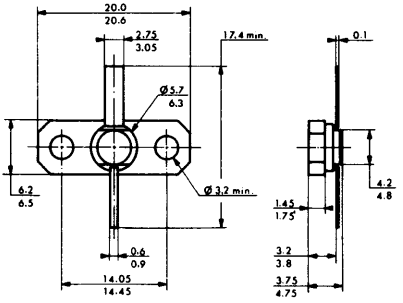
Symbols	Values			Units	Test conditions
	min.	typ.	max.		
$V_{(BR)EBO}$	3			V	I_E = 2,5 mA
$V_{(BR)CBO}$				V	I_C = mA
$V_{(BR)CES}$	50			V	I_C = 25 mA
I_{CBO}			2,5	mA	V_{CB} = 28 V
H_{FE}	15		120		I_C = 250 mA V_{CE} = 5 V
C_{22b}			5	pF	V_{CB} = 28 V f = 1 MHz

DYNAMIC CHARACTERISTICS at t_{amb} = 25°C
CARACTERISTIQUES DYNAMIQUES à t_{amb} = 25°C

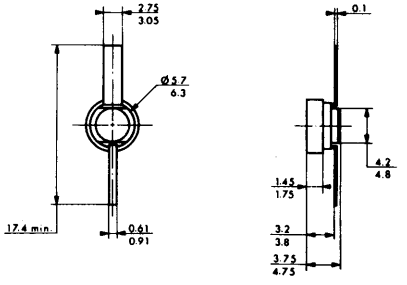
Symbols	Values			Units	Test conditions
	min.	typ.	max.		
P_{OUT}	2,5	3		W	f = 3 GHz V_{CC} = 28 V P_{IN} =0,75W
G_P	5	6		dB	f = 3 GHz V_{CC} = 28 V P_{IN} =0,75W
η_c	27	30		%	f = 3 GHz V_{CC} = 28 V P_{IN} =0,75W

CASE DESCRIPTION
DESCRIPTION DU BOITIER

CB-294 (.2502LFL/FLM, BMH 75 a)



CB-311 (.2502L/2LM, BMH 75 b)



Dimensions in millimeters

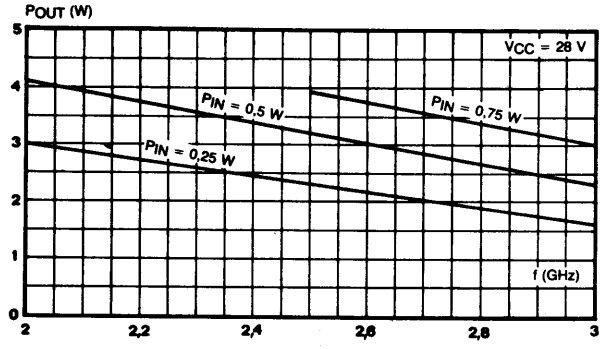


Fig. 1 - Output power versus frequency (typical values).

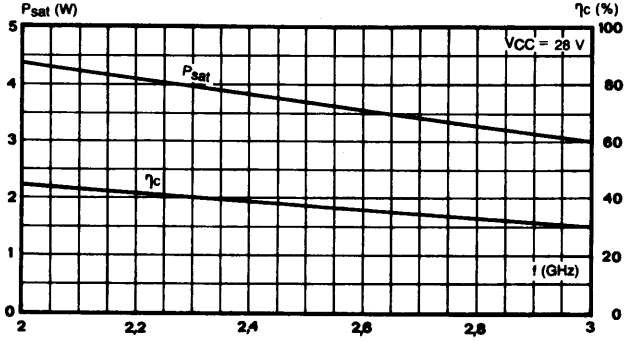


Fig. 2 - Collector efficiency and saturation power versus frequency (typical values).

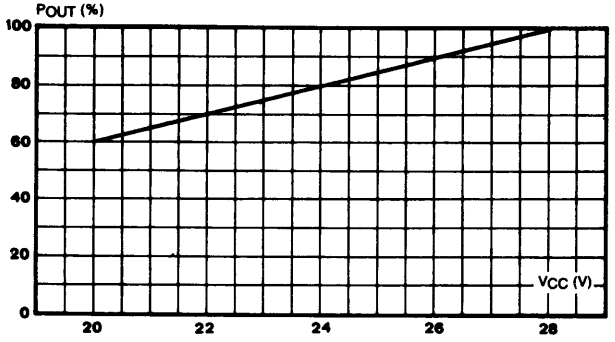


Fig. 3 - Relative output power versus collector voltage.

Z_{IN} : Input impedance
Z_{CL} : Collector load impedance

V_{CC} = 28 V
P_{IN} = 0,5 W
Z_O = 50 Ω

Fig. 4 - Smith chart

THOMSON-CSF

DIVISION SEMICONDUCTEURS DISCRETS

TH 3005

MICROWAVE NPN POWER TRANSISTOR FOR CLASS C OPERATION

TRANSISTOR NPN HYPERFREQUENCE DE PUISSANCE, CLASSE C

FEATURES

- Gold metallizations
- Glass passivated structure
- Hermetical ceramic package

→ high reliability

- Emitter ballast resistors → severe impedance mismatch
- Auto-aligned structure → high characteristics reproductibility

APPLICATIONS

Telecommunications up to 3 GHz frequency band.

PARTICULARITES

- *Métallisations "Or"*
- *Structure passivée*
- *Boîtier céramique hermétique*

→ *haute fiabilité*

- *Résistances ballast d'émetteur* → *bonne tenue au ROS*
- *Structure auto-alignée* → *bonne reproductibilité des caractéristiques*

APPLICATIONS

Télécommunications dans la bande de fréquences jusqu'à 3 GHz

f	=	3	GHz
P_{OUT}	=	5	W
G_P	=	5	dB
η_c	=	30	%
V_{CC}	=	28	V

Case / *Boîtier* : CB-294 (.2502LFL/FLM)
CB-311 (.2502L/2LM)

ABSOLUTE RATINGS (LIMITING VALUES) *VALEURS LIMITES ABSOLUES D'UTILISATION*	Symbols	Values	Units
Emitter-base (d.c.) voltage *Tension continue émetteur-base*	V_{EBO}	3	V
Collector-base (d.c.) voltage *Tension continue collecteur-base*	V_{CBO}	50	V
Collector-emitter (d.c.) voltage *Tension continue collecteur-émetteur*	V_{CES}	50	V
Collector (d.c.) current *Courant continu de collecteur*	I_C	1,5	A
Storage and junction temperature range *Températures extrêmes de stockage et de jonction*	T_{stg} T_j	— 65 → + 200 — 55 → + 200	°C °C

Thermal resistance (junction-case) *Résistance thermique (jonction-boîtier)*	$R_{th(j-c)}$	8,5	°C/W

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THOMSON-CSF COMPOSANTS

STATIC CHARACTERISTICS at t_{amb} = 25°C
CARACTERISTIQUES STATIQUES à t_{amb} = 25°C

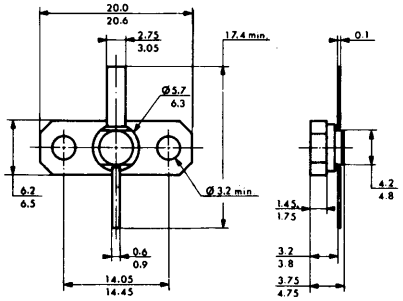
Symbols	Values			Units	Test conditions		
	min.	typ.	max.				
$V_{(BR)EBO}$	3			V	I_E = 5 mA		
$V_{(BR)CBO}$				V	I_C = mA		
$V_{(BR)CES}$	50			V	I_C = 50 mA		
I_{CBO}			5	mA	V_{CB} = 28 V		
H_{FE}	15		120		I_C = 500 mA	V_{CE} = 5 V	
C_{22b}			8	pF	V_{CB} = 28 V	f = 1 MHz	

DYNAMIC CHARACTERISTICS at t_{amb} = 25°C
CARACTERISTIQUES DYNAMIQUES à t_{amb} = 25°C

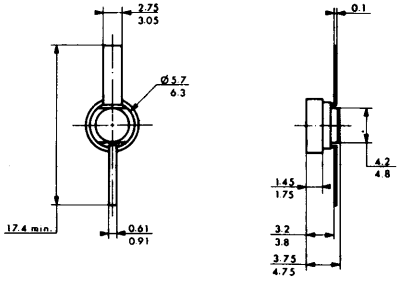
Symbols	Values			Units	Test conditions		
	min.	typ.	max.				
P_{OUT}	4,5	5		W	f = 3 GHz	V_{CC} = 28 V	P_{IN} = 1,6 W
G_P	4,5	5		dB	f = 3 GHz	V_{CC} = 28 V	P_{IN} = 1,6 W
η_c	27	30		%	f = 3 GHz	V_{CC} = 28 V	P_{IN} = 1,6 W

CASE DESCRIPTION
DESCRIPTION DU BOITIER

CB-294 (.2502LFL/FLM, BMH 75 a)



CB-311 (.2502L/2LM, BMH 75 b)



Dimensions in millimeters

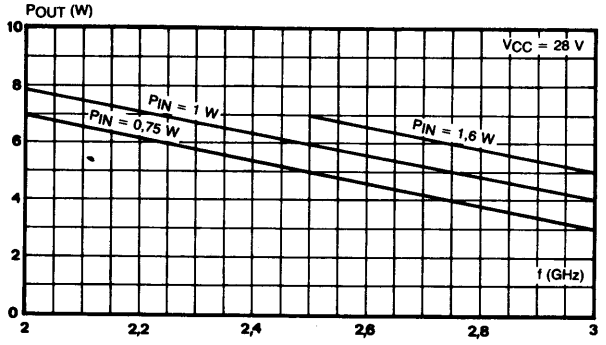


Fig. 1 - Output power versus frequency (typical values).

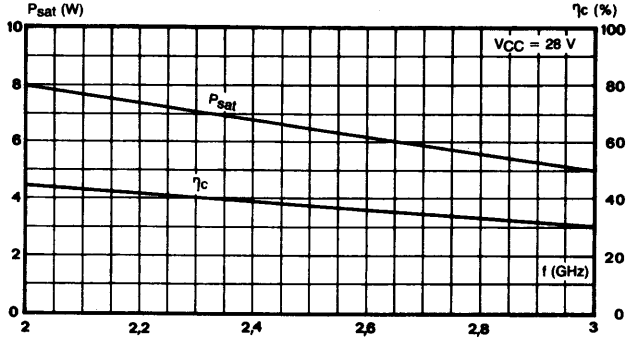


Fig. 2 - Collector efficiency and saturation power versus frequency (typical values).

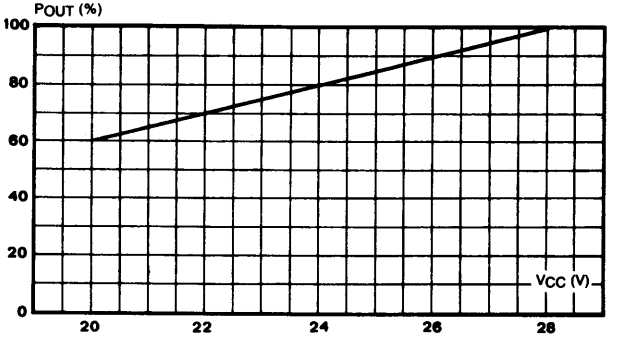


Fig. 3 - Relative output power versus collector voltage.

Z_{IN} : Input impedance
Z_{CL} : Collector load impedance

Fig. 4 - Smith chart

V_{CC} = 28 V
P_{IN} = 1 W
Z_O = 50Ω